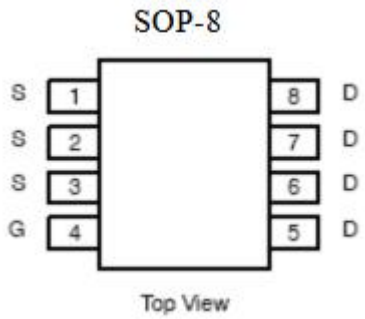
1.Features

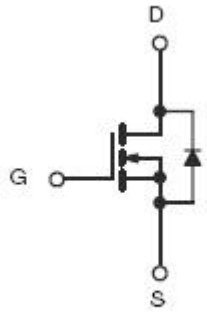
- Advanced trench process technology
- High density cell design for ultra low on-resistance
- Fully characterized avalanche voltage and current

2.Applications

- Vds=30V
- $R_{DS(ON)}$=8.0mΩ(typ.),VGS@10V,Ids@12A
- $R_{DS(ON)}$=11.5mΩ(typ.),VGS@4.5V,Ids@6A

3. Pin configuration





N-Channel MOSFET

Pin	Function
1,2,3	Source
4	Gate
5,6,7,8	Drain

4. Maximum ratings and thermal characteristics

(Ta=25°C,unless otherwise notes)

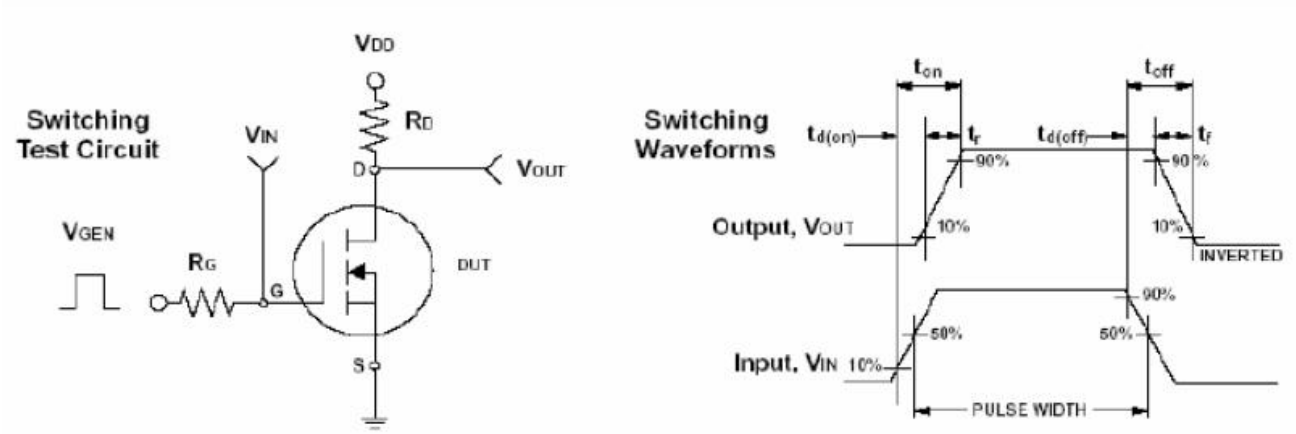
Rating		Symbol	Value	Unit
Drain-source voltage		V_{DS}	30	V
Gate-source voltage		V_{GS}	±20	V
Continuous drain current		I_D	12	A
Pulsed drain current[1)]		I_{DM}	48	A
Maximum power dissipation	T_A=25°C	P_D	3.1	W
	T_A=75°C	P_D	2.0	W
Operating junction and storage temperature range		T_J/T_{STG}	-55 to 150	°C
Junction-to-case thermal resistance		$R_{\theta JC}$	40.3	°C/W
Junction-to ambient themal rasistance (PCB mount)[2)]		$R_{\theta JA}$	59	°C/W

Note:Repetitive rating:pulse width limited by the maximum junction temperation

5. Ordering information

Part number	Package
KNE6303A	SOP-8

6. Typical application circuit



7. Electrical characteristics

(Ta=25°C,unless otherwise notes)

Parameter	Symbol	Test conditions	Min.	Typ.	Max.	Units
Static						
Drain-source breakdown voltage	BV_{DSS}	V_{GS}=0V,I_D=250μA	30	-	-	V
Drain-source on-state rasistancem	$R_{DS(ON)}$	V_{GS}=4.5V,I_D=6A	-	11.5	14.0	mΩ
		V_{GS}=10V,I_D=12A	-	8.0	10.0	mΩ
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=-250μA	1	1.8	3	V
Forward transconductance	G_{fs}	V_{DS}=15V,I_D=6A	-	12	-	S
Zero gate voltage drain current	I_{DSS}	V_{DS}=25V,V_{GS}=0V	-	-	1	μA
Gate-source forward leakage	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
Dynamic[3)]						
Total gate charge	Q_g	I_D=35A V_{DS}=15V V_{GS}=10V	-	10		nC
Gate-source charge	Q_{gs}			3.5		nC
Gate-drain (“miller”)charge	Q_{gd}		-	3		nC
Turn-on delay time	$t_{d(off)}$	V_{DD}=15V I_D=1A R_G=6Ω R_L=15Ω V_{GEN}=10V	-	12	-	ns
Rise time	t_r		-	4	-	ns
Turn-off delay time	$t_{d(off)}$		-	32	-	ns
Fall time	t_f		-	6	-	ns
Input capacitance	C_{iss}	V_{GS}=0V V_{DS}=15V f=1.0MHz	-	1300	-	pF
Output capacitance	C_{oss}		-	270	-	pF
Reverse transfer capacitance	C_{rss}		-	145	-	pF

Source-drain diode

Parameter	Symbol	Test condition	Min.	Typ.	Max.	Units
Diode forward voltage	V_{SD}	I_S=10A,V_{GS}=0V	-	0.87	1.5	V
Max.diode forward current	I_S		-	-	12	A

Notes:Pulse width≤300μs,duty cycle≤2%

8. Test circuits and waveforms

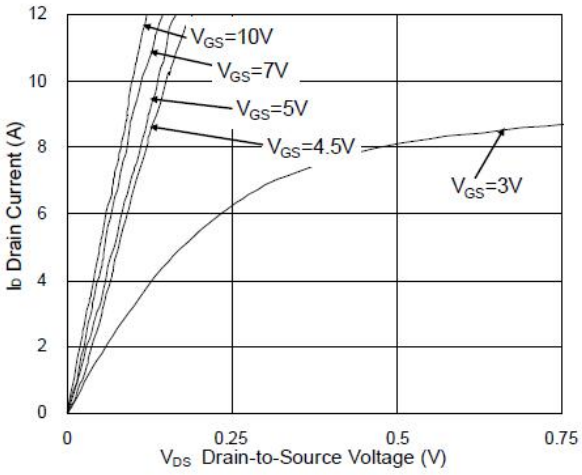


Fig.1 Typical Output Characteristics

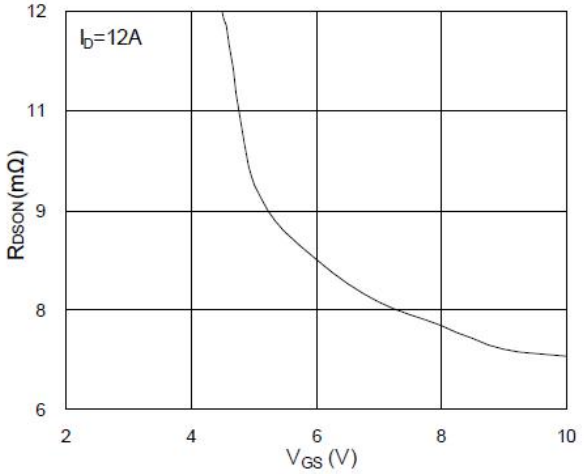


Fig.2 On-Resistance vs. G-S Voltage

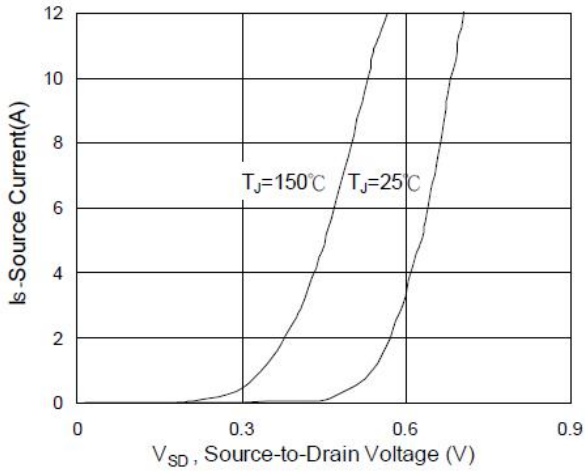


Fig.3 Forward Characteristics of Reverse

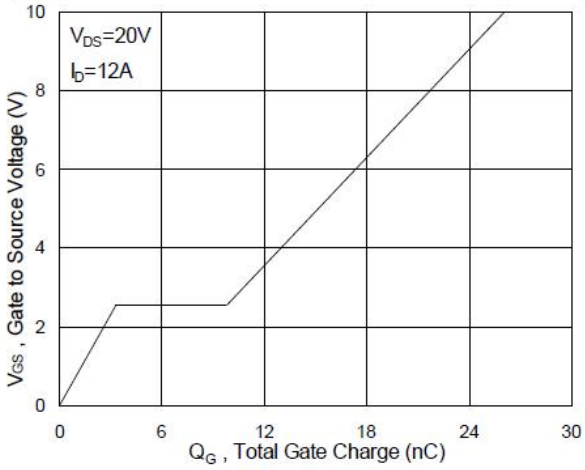


Fig.4 Gate-Charge Characteristics

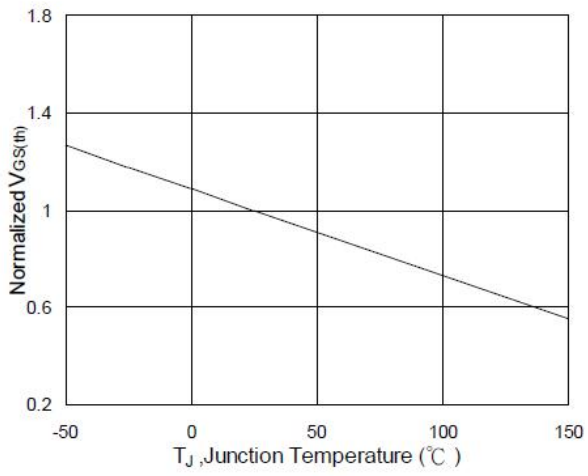


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

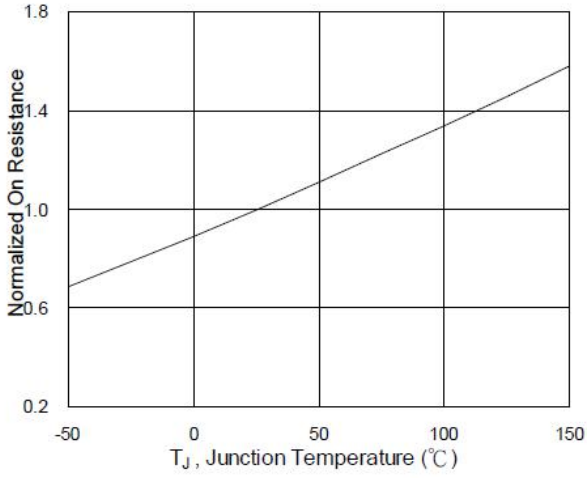


Fig.6 Normalized R_{DSON} vs. T_J

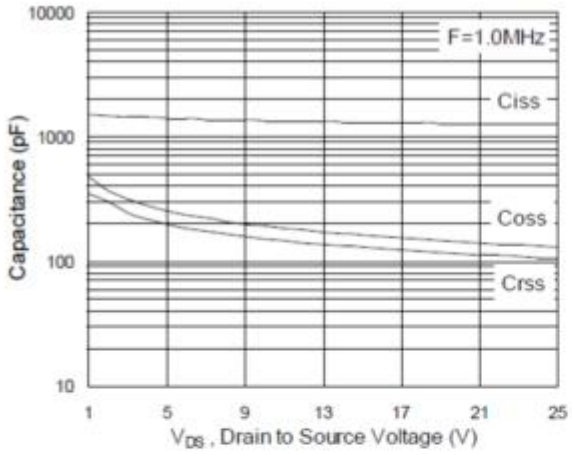


Fig.7 Capacitance

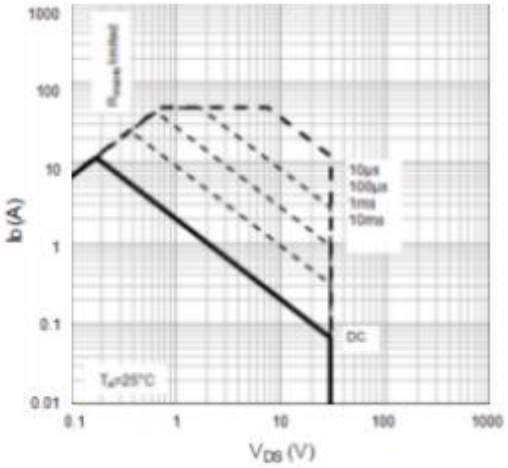


Fig.8 Safe Operating Area

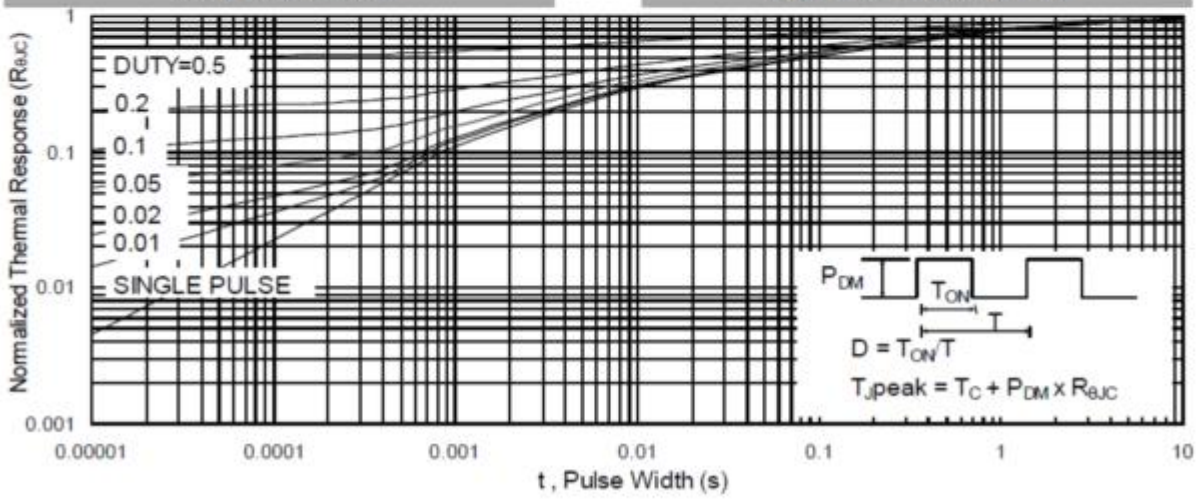


Fig.9 Normalized Maximum Transient Thermal Impedance

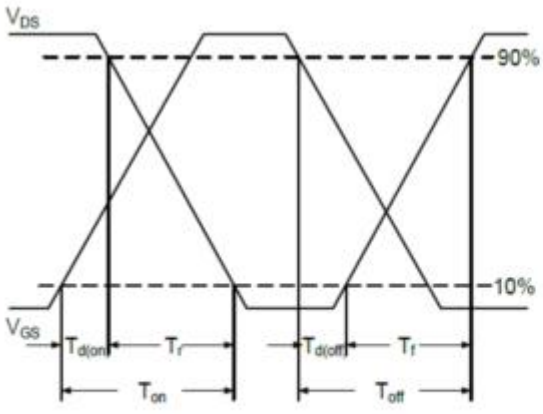


Fig.10 Switching Time Waveform

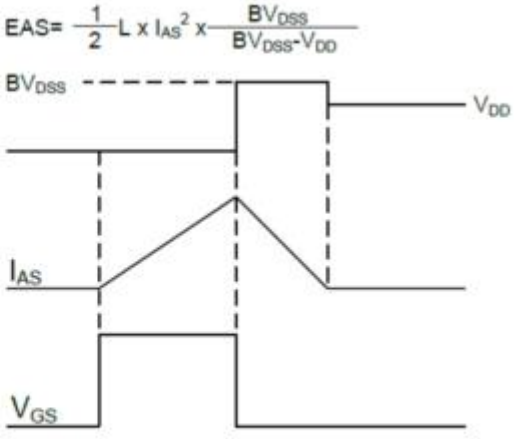


Fig.11 Unclamped Inductive Switching Waveform